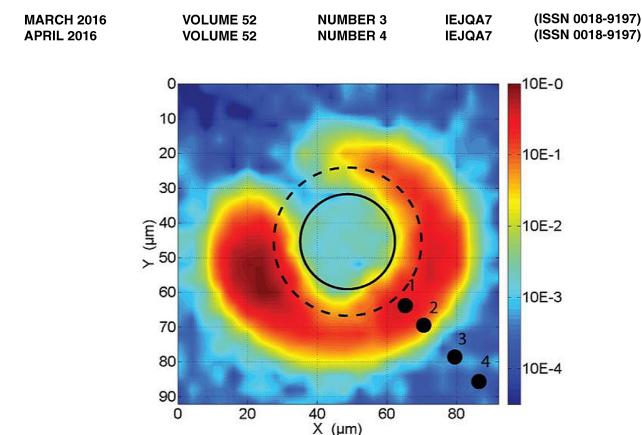
IEEE JOURNAL OF

QUANTUM ELECTRONICS

A PUBLICATION OF THE IEEE PHOTONICS SOCIETY



This Print Collection Contains the Following Issues:



Normalized maps of spurious counts when scanning the SPAD active area and its periphery with a pulsed laser stimulus before the gate with $\Delta t=10$ ns (top) and $\Delta t=100$ ns (bottom), respectively. The active area is delimited by a solid line and the edge of the shallow diffusion by the dashed line. The anode metal stripe shields the laser illumination in the top left corner of the figure. Points 1 to 4 are the four spot positions mentioned in legend of Fig. 12 and where the curves therein reported are acquired. Operating conditions: $V_{\rm EX}=5$ V, $V_{\rm UV}=0.5$ V, $T_{\rm ON}=20$ ns, $T_{\rm OFF}=100~\mu{\rm s}$, Temperature = 225 K (Calandri *et al.*, Article #4500107).

For the March 2016 issue, see Article #0100301 for the Table of Contents. For the April 2016 issue, see Article #0100401 for the Table of Contents.



IEEE JOURNAL OF

QUANTUM ELECTRONICS

MARCH 2016 VOLUME 52 NUMBER 3 IEJQA7 (ISSN 0018-9197)

REGULAR PAPERS	
Semiconductor Lasers Constriction Resistance and Current Crowding in Electrically Pumped Semiconductor Nanolasers with the Presence of Undercut and Sidewall Tilt	2000207
Surface-Emitting Semiconductor Lasers	
Direct Evidence of the Leaky Emission in Oxide-Confined Vertical Cavity Lasers	2400207
Quantum Well Lasers	
Theory and Optimization of 1.3-µm Metamorphic Quantum Well Lasers S. Bogusevschi, C. A. Broderick, and E. P. O'Reilly	2500111
Quantum Well Detectors Wavelength-Specific Ultraviolet Photodetectors Based on AlGaN Multiple Quantum Wells	4300206
Avalanche Photodiodes	
Charge Persistence in InGaAs/InP Single-Photon Avalanche Diodes N. Calandri, M. Sanzaro, A. Tosi, and F. Zappa	4500107
Nonlinear Optics and Materials	
Enhancement of Two-Photon Absorption in Quantum Wells for Extremely Nondegenerate Photon Pairs	9000114
Quantum Optics	
Electrically Controlled Quantum Memories With a Cavity and Electro-Mechanical System	9300106

IEEE JOURNAL OF QUANTUM ELECTRONICS (ISSN 0018-9197) is published monthly by The Institute of Electrical and Electronics Engineers, Inc. Responsibility for the contents rests upon the authors and not upon the IEEE, the Society/Council, or its members. IEEE Corporate Office: 3 Park Avenue, 17th Floor, New York, NY 10016-5997. IEEE Operations Center: 445 Hoes Lane, Piscataway, NJ 08854-4141. NJ Telephone: +1 732 981 0060. Price/Publication Information: Individual copies: IEEE Member \$20.00 (first copy only), nonmembers \$434.00 per copy. (Note: Postage and handling charge not included.) Member and nonmember subscription prices available upon request. Available in microfiche and microfilm. Copyright and Reprint Permissions: Abstracting is permitted with credit to the source. Libraries are permitted to photocopy for private use of patrons, provided the per-copy fee of \$31.00 is paid through the Copyright Clearance Center, 222 Rosewood Drive, Danvers, MA 01923. For all other copying, reprint, or republication permission, write to Copyrights and Permissions Department, IEEE Publications Administration, 445 Hoes Lane, Piscataway, NJ 08854-4141. Copyright © 2016 by The Institute of Electrical and Electronics Engineers, Inc. All rights reserved. Postmaster: Send address changes to IEEE JOURNAL OF QUANTUM ELECTRONICS, IEEE, 445 Hoes Lane, Piscataway, NJ 08854-4141. GST Registration No. 125634188. IEEE prohibits discrimination, harassment and bullying. For more information visit http: www.ieee.org/nondiscrimination. Printed in U.S.A.